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## GaN on SiC HEMT Pulsed Power Transistor 180 W Peak, 2700 to 3100 MHz, 300 µs Pulse, 10% Duty

Rev. V6

#### **Features**

- GaN Depletion Mode HEMT Microwave Transistor
- Common Source Configuration
- · Broadband Class AB Operation
- Thermally Enhanced Cu/Mo/Cu Package
- RoHS Compliant
- +50 V Typical Operation
- MTTF of 600 Years (T<sub>.1</sub> < 200°C)</li>
- EAR99 Export Classification

### **Applications**

· Civilian and Military Pulsed Radar

### Description

The MAGX-002731-180L00 and MAGX-002731-180L0S are gold metalized matched Gallium Nitride (GaN) on Silicon Carbide RF power transistors optimized for civilian and military radar pulsed applications between 2700 - 3100 MHz.

Using state of the art wafer fabrication processes, these high performance transistors provide high gain, efficiency, bandwidth, ruggedness over a wide bandwidth for today's demanding application needs.

The MAGX-002731-180L00 and MAGX-002731-180L0S are constructed using thermally enhanced Cu/Mo/Cu flanged ceramic packages which provide excellent thermal performance. High breakdown voltages allow for reliable and stable operation in extreme mismatched load conditions unparalleled with older semiconductor technologies.

#### MAGX-002731-180L00



#### MAGX-002731-180L0S



## Ordering Information<sup>1</sup>

Part Number	Package
MAGX-002731-180L00	Standard Flange
MAGX-002731-180L0S	Earless Flange
MAGX-S32731-180L00	2700 – 3100 MHz Evaluation Board

- When ordering the evaluation board, please indicate on sales order notes if it will be used for:
  - A. Standard Flange devices
  - B. Earless Flange devices



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## Electrical Specifications<sup>2</sup>: 2700 - 3100 MHz, T<sub>A</sub> = 25°C

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Units
RF Functional Tests: V <sub>DD</sub> = 50 V, I <sub>DQ</sub> = 500 mA, 300 μs Pulse, 10% Duty Cycle						
Output Power	P <sub>IN</sub> = 14 Wpk	P <sub>OUT</sub>	180	215	-	Wpk
Gain	P <sub>IN</sub> = 14 Wpk	G <sub>P</sub>	11.1	11.8	-	dB
Drain Efficiency	P <sub>IN</sub> = 14 Wpk	η <sub>D</sub>	43	51	-	%
Load Mismatch Stability	P <sub>IN</sub> = 14 Wpk	VSWR-S	-	5:1	-	-
Load Mismatch Tolerance	P <sub>IN</sub> = 14 Wpk	VSWR-T	-	10:1	-	-

<sup>2.</sup> Typical RF performance measured in an RF evaluation board.

## Electrical Characteristics: $T_A = 25$ °C

Parameter	Test Conditions	Symbol	Min.	Тур.	Max.	Units
DC Characteristics						
Drain-Source Leakage Current	V <sub>GS</sub> = -8 V, V <sub>DS</sub> = 175 V	I <sub>DS</sub>	-	-	12	mA
Gate Threshold Voltage	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 30 mA	V <sub>GS (TH)</sub>	-5	-3	-2	V
Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 3.5 mA	G <sub>M</sub>	5	-	-	S
Dynamic Characteristics						
Input Capacitance	N/A - Input Internally Matched	C <sub>ISS</sub>	N/A	N/A	N/A	pF
Output Capacitance	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = -8 V, F = 1 MHz	Coss	-	26.1	30.3	pF
Reverse Transfer Capacitance	V <sub>DS</sub> = 50 V, V <sub>GS</sub> = -8 V, F = 1 MHz	C <sub>RSS</sub>	-	2.3	4.7	pF



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## **Absolute Maximum Ratings**<sup>3,4,5</sup>

Parameter	Absolute Maximum	
Drain Supply Voltage (V <sub>DD</sub> )	+65 V	
Gate Supply Voltage (V <sub>GG</sub> )	-8 V to 0 V	
Drain Supply Current (I <sub>D</sub> )	10 A	
Input Power <sup>6</sup> (P <sub>IN</sub> )	P <sub>IN</sub> (nominal) + 3 dB	
Operating Junction Temperature <sup>7</sup>	250°C	
Peak Pulsed Power Dissipation @ 85°C	192 W	
Operating Temperature	-40°C to +85°C	
Storage Temperature	-65°C to +150°C	
ESD Min Charged Device Model (CDM)	350 V	
ESD Min Human Body Model (HBM)	550 V	
Maximum Solder Temperature	260°C	

<sup>3.</sup> Exceeding any one or combination of these limits may cause permanent damage to this device.

#### **Thermal Characteristics**

Parameter	Test Conditions		Typical	Units
Thermal Resistance	$T_C$ = 85°C, $V_{DD}$ = 50 V, $I_{DQ}$ = 500 mA Pulse Width = 500 µs, Duty Cycle = 10%	$\Theta_{JC}$	0.6	°C/W

<sup>4.</sup> MACOM does not recommend sustained operation near these survivability limits.

<sup>5.</sup> For saturated performance it is recommended that the sum of (3 \*  $V_{DD}$  +  $|V_{GG}|$ ) < 175 V.

<sup>6.</sup> Input Power Limit is +3 dB over nominal drive required to achieve P<sub>OUT</sub> = 180 W.

<sup>7.</sup> Operating junction temperature is measured with infrared (IR) microscope. Junction temperature directly affects a device's MTTF and should be kept as low as possible to maximize lifetime.

<sup>•</sup> MTTF =  $5.3 \times 10^6$  hours (T<sub>J</sub> <  $200^{\circ}$ C)

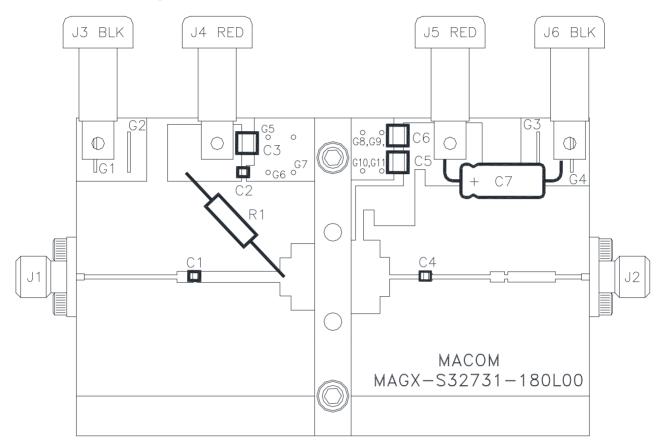
MTTF = 6.8 x 10<sup>4</sup> hours (T<sub>J</sub> < 250°C)</li>



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## **Test Fixture Assembly**



#### **Parts List**

Part	Description		
C1, C2, C4	Capacitor, 12 pF, 250 V, 5%, ATC800A		
C3, C5	Capacitor, 0.1 μF, 100 V, 10%, X7R, 0805, TDK		
C6	Capacitor, 1.0 μF, 100 V, 5%, 1206, Murata		
C7	Capacitor, 22 μF, 100 V, 20%, Panasonic		
R1	Resistor, 12 ohm, 1/4 W, 1%, Axial, Vishay Dale		
J1, J2	SMA Connector		
J3, J6	Female Banana Jack, Black		
J4, J5	Female Banana Jack, Red		
PCB	MACOM (Rogers RT6010.5LM, 0.25" thick, Er = 10.5)		



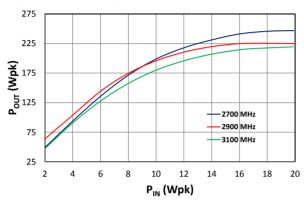
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## **Applications Section**

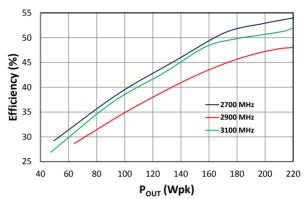
## **Typical Large-Signal Performance Curves**

2700 - 3100 MHz, 300 μs Pulse, 10% Duty Cycle,  $V_{DD}$  = 50 V,  $I_{DQ}$  = 500 mA,  $P_{IN}$  = 14 Wpk,  $T_A$  = 25°C

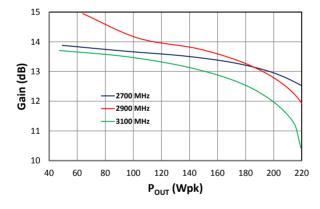
#### Output Power vs. Input Power



#### Drain Efficiency vs. Output Power



#### Gain vs. Output Power





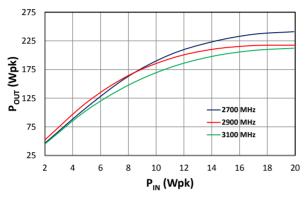
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## **Applications Section**

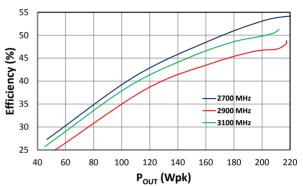
## **Typical Large-Signal Performance Curves**

2700 - 3100 MHz, 500 μs Pulse, 10% Duty Cycle,  $V_{DD}$  = 50 V,  $I_{DQ}$  = 500 mA,  $P_{IN}$  = 14 Wpk,  $T_A$  = 25°C

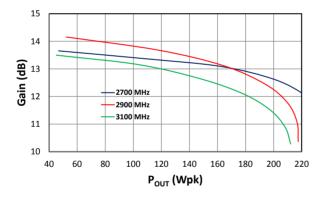
### Output Power vs. Input Power



#### Drain Efficiency vs. Output Power



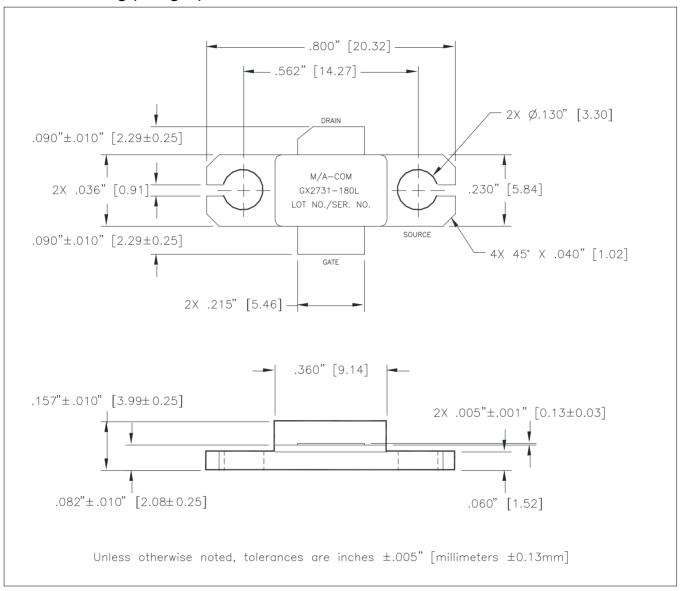
#### Gain vs. Output Power





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## **Outline Drawing (Flanged)**



## **Bias Sequencing**

#### TURNING THE DEVICE ON

- 1. Set  $V_{GS}$  to the pinch-off  $(V_P)$ , typically -5 V.
- 2. Turn on V<sub>DS</sub> to nominal voltage (50 V).
- 3. Increase  $V_{\text{GS}}$  until the  $I_{\text{DS}}$  current is reached .
- 4. Apply RF power to desired level.

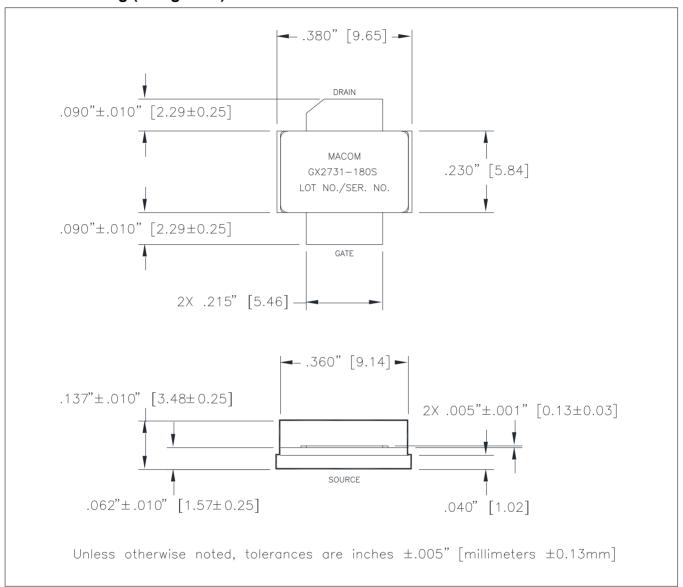
#### **TURNING THE DEVICE OFF**

- 1. Turn the RF power off.
- 2. Decrease  $V_{GS}$  down to  $V_{P.}$
- 3. Decrease V<sub>DS</sub> down to 0 V.
- 4. Turn off V<sub>GS</sub>



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### **Outline Drawing (Flangeless)**





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